



The DNA of tech.™

Product Information Notification



Product Group: DD/Monday August 3, 2026/PIN-DD-018-2026-REV-0

Typo corrections on some SOT-227 datasheets

For further information, please contact your regional Vishay office.

CONTACT INFORMATION

Americas

Vishay Semiconductors
One Greenwich Place
-
Shelton CT United States 06484
Phone: +1 402 563 6866
Fax: +1 402 563 6296
Diodes-Americas@vishay.com

Europe

Vishay Semiconductors
Theresienstrasse 2
-
Heilbronn Germany 74072
Phone: +49 7131 7498 656 (715)
Fax: +49 7131 67 2938
Diodes-Europe@vishay.com

Asia

Vishay Semiconductors
37A Tampines Street 92 #07-01
-
Singapore 528886
Phone: +65 6788 6668
Fax: +65 6788 988
Diodes-Asia@vishay.com

Description of Change: Vishay Semiconductors communicates some typos correction into the datasheet of few SOT-227 part number. See Annex 1 for the details.

Reason for Change: Typo correction

Expected Influence on Quality/Reliability/Performance: There will be no effect on product quality, reliability or performance.

Part Numbers/Series/Families Affected: VS-SC160FA65, VS-SC240FA120,

Vishay Brand(S): Vishay Semiconductors

Time Schedule:

Start Shipment Date: Monday August 3, 2026

Sample Availability: Samples available upon request

Product Identification: Batch code (contact factory for the details)

Qualification Data: Available upon request

Issued By: Fabio Bertuccio, fabio.bertuccio@vishay.com

ANNEX 1

ELECTRICAL SPECIFICATIONS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	$I_R = 400\ \mu\text{A}$	650	-	-	V
Forward voltage	V_{FM}	$I_F = 80\ \text{A}$	-	1.38	1.59	
		$I_F = 80\ \text{A}$, $T_J = 150^\circ\text{C}$	-	1.61	-	
Reverse leakage current	I_{RM}	$V_R = 650\ \text{V}$	-	3.7	1.60 	μA
		$T_J = 125^\circ\text{C}$, $V_R = 650\ \text{V}$	-	12.6	-	
		$T_J = 150^\circ\text{C}$, $V_R = 650\ \text{V}$	-	18.7	-	
Junction capacitance	C_T	$V_R = 650\ \text{V}$, $f = 1\ \text{MHz}$	-	318	-	pF

Revision: 15-Apr-2024

1

Document Number: 97139

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT
ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



www.vishay.com

VS-SC160FA65

Vishay Semiconductors

ELECTRICAL SPECIFICATIONS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	$I_R = 100\ \mu\text{A}$	1200	-	-	V
Forward voltage	V_{FM}	$I_F = 120\ \text{A}$	-	1.45	1.63	
		$I_F = 120\ \text{A}$, $T_J = 150^\circ\text{C}$	-	1.89	-	
Reverse leakage current	I_{RM}	$V_R = 1200\ \text{V}$	-	5.69		μA
		$T_J = 125^\circ\text{C}$, $V_R = 1200\ \text{V}$	-	21.03	-	
		$T_J = 150^\circ\text{C}$, $V_R = 1200\ \text{V}$	-	31.25	-	
Junction capacitance	C_T	$V_R = 1200\ \text{V}$, $f = 1\ \text{MHz}$	-	410	-	pF

Revision: 15-Apr-2024

1

Document Number: 97151

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT
ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



www.vishay.com

VS-SC240FA120

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total capacitive charge	Q_C	$V_R = 800\ \text{V}$	-	651	-	nC